



High Efficiency Thyristor

$V_{RRM} = 800\text{ V}$

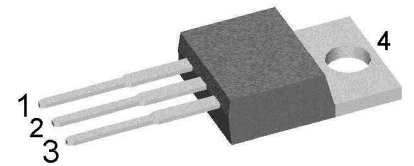
$I_{TAV} = 20\text{ A}$

$V_T = 1.31\text{ V}$

Single Thyristor

Part number

CS19-08ho1



Backside: anode



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-220

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

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Thyristor				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			900	V	
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			800	V	
I_{RD}	reverse current, drain current	$V_{R/D} = 800 V$	$T_{VJ} = 25^{\circ}C$		50	μA	
		$V_{R/D} = 800 V$	$T_{VJ} = 125^{\circ}C$		1	mA	
V_T	forward voltage drop	$I_T = 20 A$	$T_{VJ} = 25^{\circ}C$		1.32	V	
		$I_T = 40 A$			1.65	V	
		$I_T = 20 A$	$T_{VJ} = 125^{\circ}C$		1.31	V	
		$I_T = 40 A$			1.73	V	
I_{TAV}	average forward current	$T_C = 110^{\circ}C$	$T_{VJ} = 125^{\circ}C$		20	A	
$I_{T(RMS)}$	RMS forward current	180° sine			31	A	
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 125^{\circ}C$		0.86	V	
r_T	slope resistance				22	m Ω	
R_{thJC}	thermal resistance junction to case				0.7	K/W	
R_{thCH}	thermal resistance case to heatsink			0.5		K/W	
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		170	W	
I_{TSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		180	A	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		195	A	
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 125^{\circ}C$		155	A	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		165	A	
I^2t	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		160	A ² s	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		160	A ² s	
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 125^{\circ}C$		120	A ² s	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		115	A ² s	
C_J	junction capacitance	$V_R = 230 V \quad f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$	9		pF	
P_{GM}	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 125^{\circ}C$		5	W	
		$t_p = 300 \mu s$			2.5	W	
P_{GAV}	average gate power dissipation				0.5	W	
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 150^{\circ}C; f = 50 \text{ Hz}$	repetitive, $I_T = 60 A$		150	A/ μs	
		$t_p = 200 \mu s; di_G/dt = 0.15 A/\mu s;$ $I_G = 0.15 A; V = \frac{2}{3} V_{DRM}$	non-repet., $I_T = 20 A$		500	A/ μs	
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 150^{\circ}C$		500	V/ μs	
		$R_{GK} = \infty; \text{method 1 (linear voltage rise)}$					
V_{GT}	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		1.5	V	
			$T_{VJ} = -40^{\circ}C$		2.5	V	
I_{GT}	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		28	mA	
			$T_{VJ} = -40^{\circ}C$		50	mA	
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 150^{\circ}C$		0.2	V	
I_{GD}	gate non-trigger current				3	mA	
I_L	latching current	$t_p = 10 \mu s$	$T_{VJ} = 25^{\circ}C$		75	mA	
		$I_G = 0.1 A; di_G/dt = 0.1 A/\mu s$					
I_H	holding current	$V_D = 6 V \quad R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		50	mA	
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}C$		2	μs	
		$I_G = 0.1 A; di_G/dt = 0.1 A/\mu s$					
t_q	turn-off time	$V_R = 100 V; I_T = 20 A; V = \frac{2}{3} V_{DRM}$ $di/dt = 10 A/\mu s \quad dv/dt = 20 V/\mu s \quad t_p = 200 \mu s$	$T_{VJ} = 100^{\circ}C$	150		μs	



Package TO-220			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			35	A
T_{VJ}	virtual junction temperature		-40		125	°C
T_{op}	operation temperature		-40		100	°C
T_{stg}	storage temperature		-40		150	°C
Weight				2		g
M_D	mounting torque		0.4		0.6	Nm
F_C	mounting force with clip		20		60	N

Product Marking



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	CS19-08ho1	CS19-08ho1	Tube	50	471038

Similar Part	Package	Voltage class
CS19-08ho1S	TO-263AB (D2Pak) (2)	800
CS19-12ho1	TO-220AB (3)	1200
CS19-12ho1S	TO-263AB (D2Pak) (2)	1200

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 125^{\circ}C$

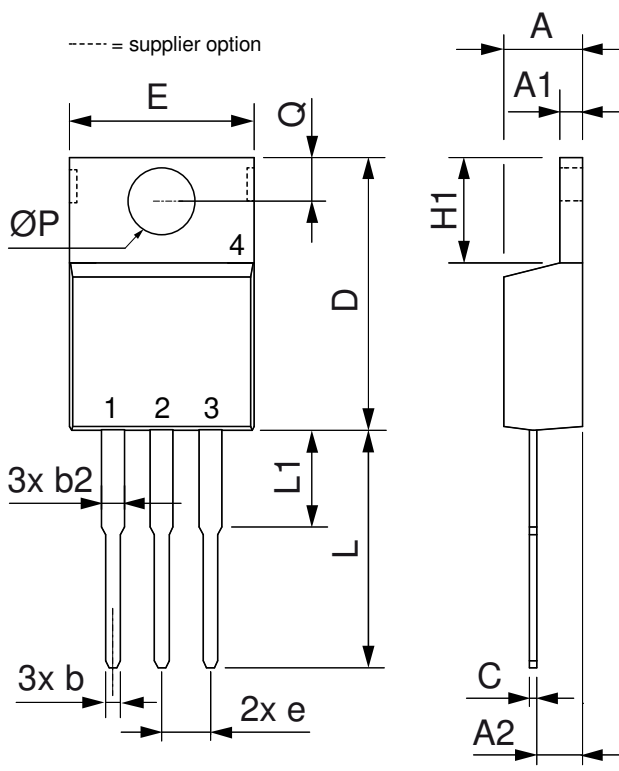


Thyristor

$V_{0\ max}$	threshold voltage	0.86	V
$R_{0\ max}$	slope resistance *	19	mΩ



Outlines TO-220



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
C	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
e	2.54	BSC	0.100	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125



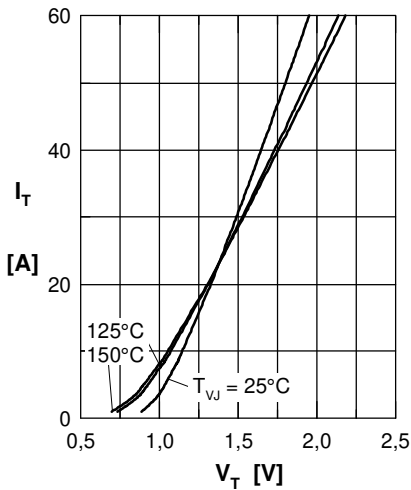
Thyristor


Fig. 1 Forward characteristics

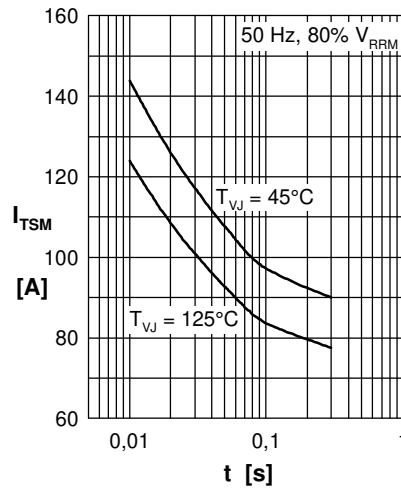


Fig. 2 Surge overload current

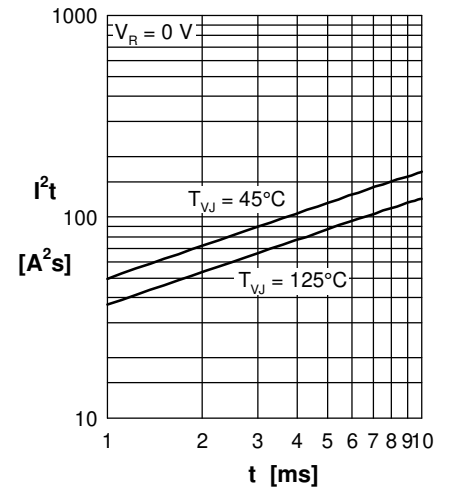
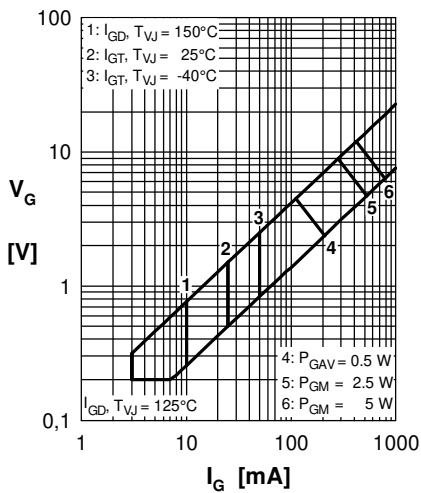

 Fig. 3 I^2t versus time (1-10 ms)


Fig. 4 Gate trigger characteristics



Fig. 5 Gate controlled delay time

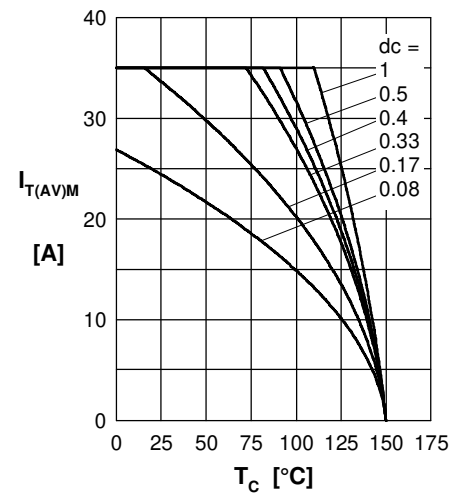


Fig. 6 Max. forward current at case temperature

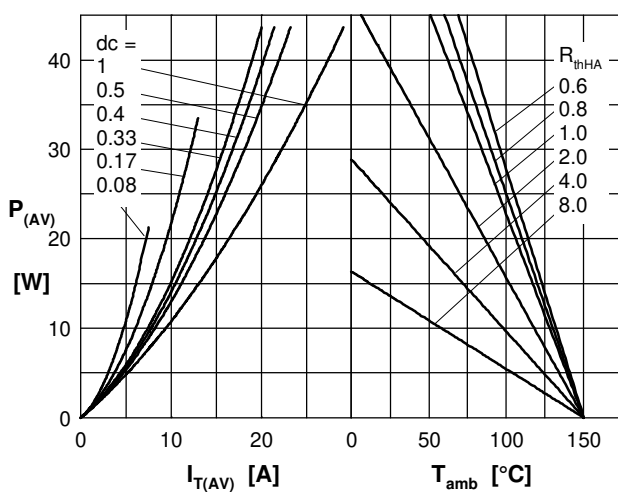
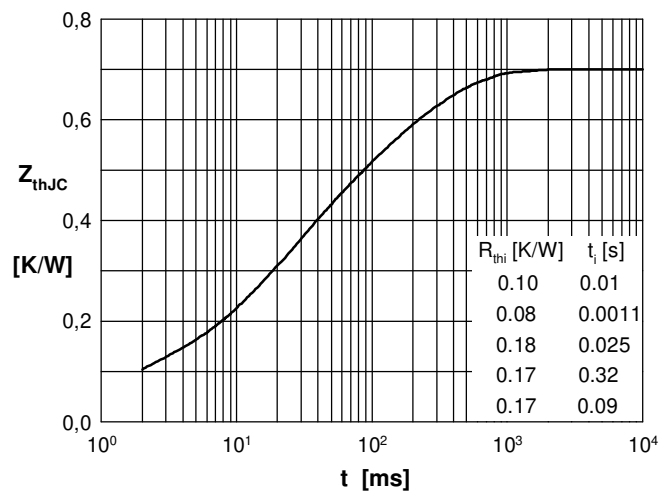

 Fig. 7a Power dissipation versus direct output current
 Fig. 7b and ambient temperature


Fig. 8 Transient thermal impedance junction to case



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